



Description

This Bipolar Junction Transistor (BJT) has been designed to meet the stringent requirements of Automotive Applications.

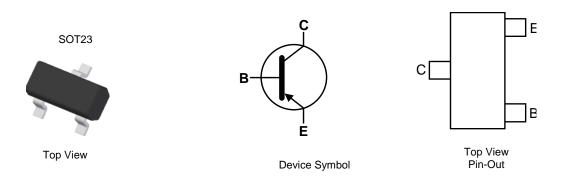
Features

- BV_{CEO} > -60V
- I_C = -1A High Continuous Collector Current
- I_{CM} = -2A Peak Pulse Current
- R_{SAT} = 295mΩ for a Low Equivalent On-Resistance
- hFE Characterized up to -2A for High Current Gain Hold Up
- Complementary NPN Type: FMMT491Q
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

60V PNP MEDIUM POWER TRANSISTOR IN SOT23

Mechanical Data

- Case: SOT23
- Case Material: molded plastic, "Green" Molding Compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (23)
- Weight: 0.008 grams (Approximate)



Ordering Information (Notes 4 & 5)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
FMMT591QTA	Automotive	591	7	8	3,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

Notes:

and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



^{2.} See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-80	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-1	А
Peak Pulse Current	ICM	-2	A
Base Current	IB	-200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 6)	PD	500	mW
Thermal Resistance, Junction to Ambient	(Note 6)	R _{θJA}	250	°C/W
Thermal Resistance, Junction to Lead (Note 7)		R _{θJL}	197	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C	

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

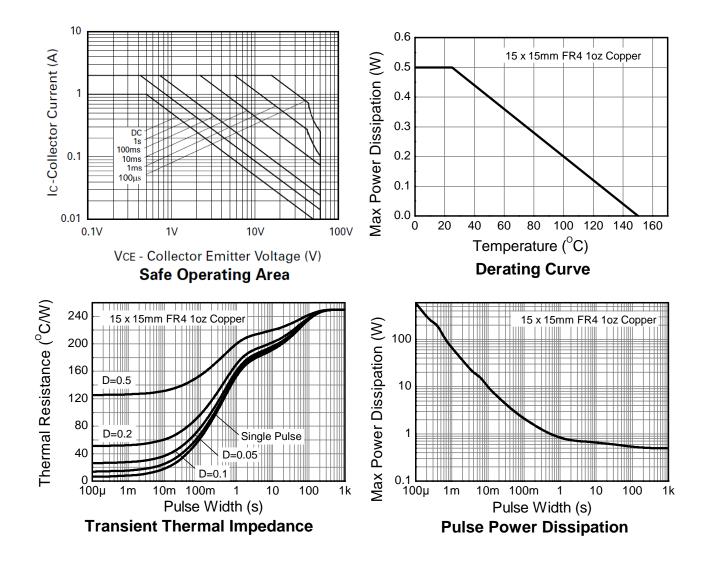
Notes: 6. For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

7. Thermal resistance from junction to solder-point (at the end of the collector lead).

8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





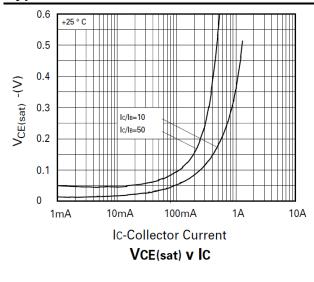
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

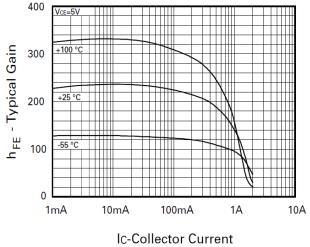
Cha	aracteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		BV _{CBO}	-80	—	_	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 9)		BV _{CEO}	-60	—	_	V	I _C = -10mA
Emitter-Base Breakd	own Voltage	BV _{EBO}	-7	-8.1	_	V	I _E = -100μA
Collector-Base Cutof	f Current	I _{CBO}	_	<1	-100	nA	V _{CB} = -60V
Emitter-Base Cutoff	Current	I _{EBO}	_	<1	-100	nA	V _{EB} = -5.6V
Collector-Emitter Cut	-Off Current	I _{CES}	_	<1	-100	nA	V _{CE} = -50V
Static Forward Current Transfer Ratio (Note 9)		hfe	100 100 80 15	220 175 155 40	 300 	_	$I_{C} = -1mA, V_{CE} = -5V$ $I_{C} = -500mA, V_{CE} = -5V$ $I_{C} = -1A, V_{CE} = -5V$ $I_{C} = -2A, V_{CE} = -5V$
Collector-Emitter Saturation Voltage (Note 9)		V _{CE(SAT)}	_	-155 -295	-180 -350	mV	I _C = - 500mA, I _B = -50mA I _C = - 1A, I _B = -100mA
Base-Emitter Saturation Voltage (Note 9)		V _{BE(SAT)}	_	965	-1200	mV	I _C = -1A, I _B = -100mA
Base-Emitter Turn-On Voltage (Note 9)		V _{BE(ON)}	_	830	-1000	mV	I _C = -1A, V _{CE} = -5V
Transition Frequency		f⊤	150	_	_	MHz	$V_{CE} = -10V, I_C = -50mA,$ f = 100MHz
Output Capacitance		C _{obo}	_	_	10	pF	V _{CB} = -10V, f = 1MHz
Switching Time	Delay Time	t _d	_	29.1	—		
	Rise Time	tr	_	26.5	—		V _{CC} = -10V, I _C = -500mA,
	Storage Time	ts	_	99.3	—	ns	$I_{B1} = -I_{B2} = -25mA$
	Fall Time	t _f	_	18.9	—	1	

Note: 9. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.

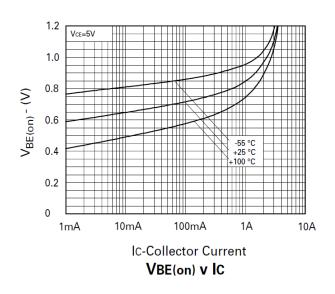


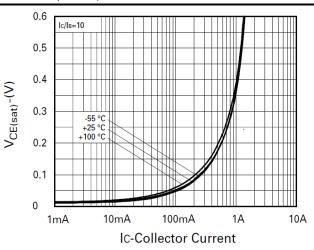
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



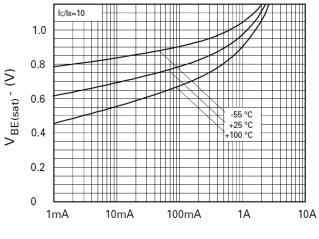


hfe V IC





VCE(sat) v lc



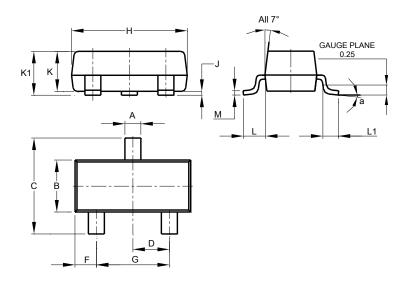
Ic-Collector Current VBE(sat) v Ic



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

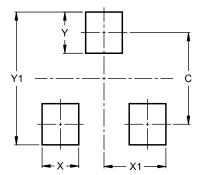


SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.890	1.00	0.975		
K1	0.903	1.10	1.025		
L	0.45	0.61	0.55		
L1	0.25	0.55	0.40		
М	0.085	0.150	0.110		
а	0°	8°			
All	All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)		
С	2.0		
Х	0.8		
X1	1.35		
Y	0.9		
Y1	2.9		



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